

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBFR42/43(RoHs Device)

$I_o = 200 \text{ mA}$

$V_R = 30 \text{ Volts}$



Features

Low forward Voltage.

Designed for mounting on small surface.

Extremely thin / leadless package.

Majority carrier conduction.

Mechanical data

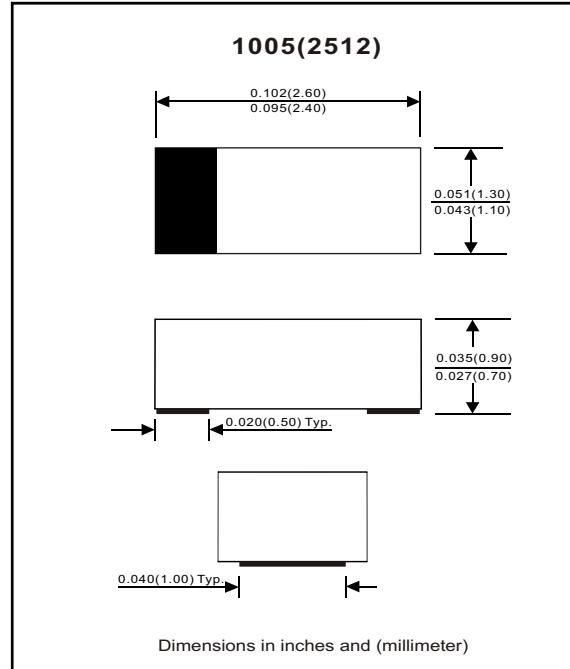
Case: 1005(2512) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.006 gram(approx.).



Maximum Rating (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Peak reverse voltage		V_{RM}			30	V
Reverse voltage		V_R			30	V
RMS reverse voltage		$V_R(\text{RMS})$			21	V
Average forward rectified current		I_o			200	mA
Repetitive peak forward current		I_{FRM}			0.5	A
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}			4	A
Power Dissipation		P_D			200	mW
Thermal resistance junction to ambient air		$R_{\theta JA}$			500	°C/W
Storage temperature		T_{STG}	-55		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage CDBFR42/43	$I_F = 200\text{mA}$	V_F			1	V
CDBFR42	$I_F = 10\text{mA}$				0.4	
CDBFR42	$I_F = 50\text{mA}$				0.65	
CDBFR43	$I_F = 2\text{mA}$				0.33	
CDBFR43	$I_F = 15\text{mA}$				0.45	
Reverse current	$V_R = 25\text{V}$	I_R			0.5	uA
Capacitance between terminals	$f = 1 \text{ MHz}, \text{and } 1 \text{ VDC reverse voltage}$	C_T			10	pF
Reverse recovery time	$I_F=I_R=10\text{mA}, I_{RR}=0.1 \times I_R, R_L=100 \text{ ohm}$	T_{rr}			5	nS

REV:A

RATING AND CHARACTERISTIC CURVES (CDBFR42/43)

Fig. 1 - Forward characteristics

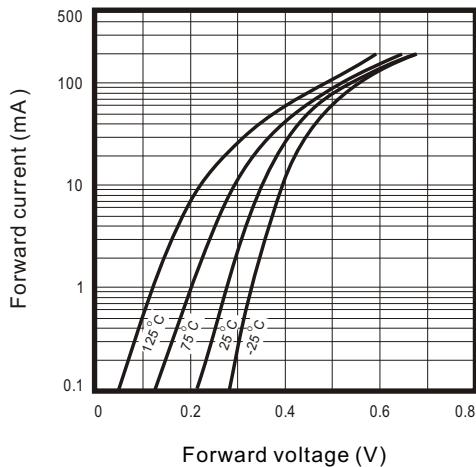


Fig. 2 - Reverse characteristics

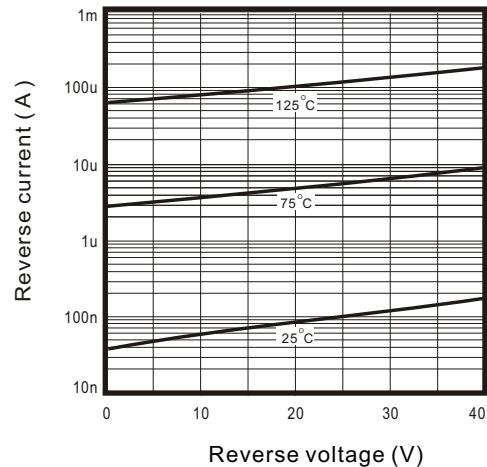


Fig.3 - Capacitance between terminals characteristics

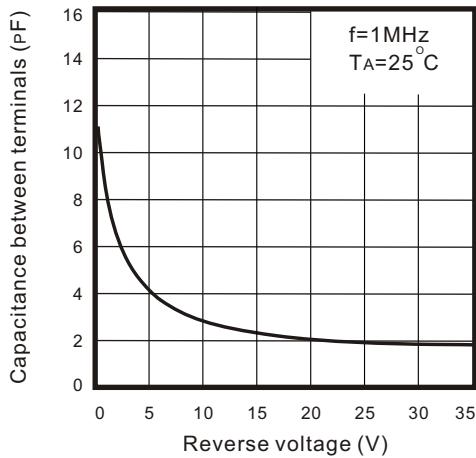


Fig.4 - Current derating curve

